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Kind regards,

Team Nexperia



2PB709ART 45 V, 100 mA PNP general-purpose transistor Rev. 01 — 19 March 2007

Product data sheet

1. Product profile

1.1 General description

PNP general-purpose transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: 2PD601ART.

1.2 Features

- General-purpose transistor
- Small SMD plastic package

1.3 Applications

General-purpose switching and amplification

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-45	V
l _C	collector current		-	-	-100	mA
h _{FE}	DC current gain	V _{CE} = -10 V; I _C = -2 mA	210	-	340	

2. Pinning information

Pin	Description	Simplified outline	Symbol
1	base		
2	emitter		3
3	collector		
			sym013



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3. Ordering information

Table 3. Order	Ordering information					
Type number	Package					
	Name	Description	Version			
2PB709ART	-	plastic surface-mounted package; 3 leads	SOT23			

4. Marking

Table 4. Ma	rking codes	
Type number	М	larking code ^[1]
2PB709ART	C	5*
21 87 007 411		

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

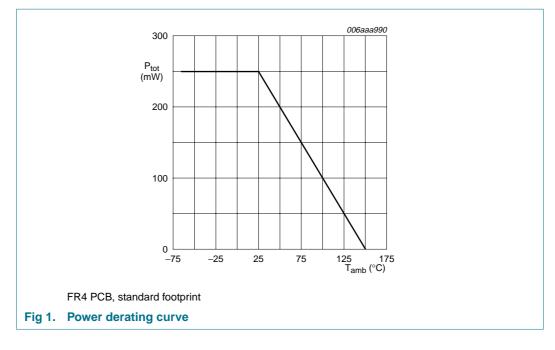
Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

$\begin{array}{cccc} V_{CBO} & \mbox{collector-base voltage} & \mbox{open emitter} & - & -45 & V \\ \hline V_{CEO} & \mbox{collector-emitter voltage} & \mbox{open base} & - & -45 & V \\ \hline V_{EBO} & \mbox{emitter-base voltage} & \mbox{open collector} & - & -6 & V \\ \hline I_C & \mbox{collector current} & \mbox{single pulse;} & - & -100 & \mbox{mA} \\ \hline I_{CM} & \mbox{peak collector current} & \mbox{single pulse;} & - & -200 & \mbox{mA} \\ \hline I_{BM} & \mbox{peak base current} & \mbox{single pulse;} & - & -100 & \mbox{mA} \\ \hline I_{bm} & \mbox{peak base current} & \mbox{single pulse;} & - & -100 & \mbox{mA} \\ \hline I_{t_p} \leq 1 \ \mbox{ms} & \mbox$	Symbol	Parameter	Conditions	Min	Max	Unit
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	V _{CBO}	collector-base voltage	open emitter	-	-45	V
I_LBCcollector current100mAI_Ccollector currentsingle pulse; $t_p \le 1 \text{ ms}$ 200mAI_BMpeak base currentsingle pulse; $t_p \le 1 \text{ ms}$ 100mAP_tottotal power dissipationT_amb $\le 25 \text{ °C}$ 11-250mWTjjunction temperature-150°CT_ambambient temperature-65+150°C	V _{CEO}	collector-emitter voltage	open base	-	-45	V
$ I_{CM} \qquad \mbox{peak collector current} \qquad \mbox{single pulse;} \\ t_p \le 1 \mbox{ ms} \qquad \mbox{-} 200 \qquad \mbox{mA} \\ I_{BM} \qquad \mbox{peak base current} \qquad \mbox{single pulse;} \\ t_p \le 1 \mbox{ ms} \qquad \mbox{-} -100 \qquad \mbox{mA} \\ P_{tot} \qquad \mbox{total power dissipation} \qquad \mbox{T}_{amb} \le 25 \ ^{\circ}\text{C} \qquad \mbox{11} \ \mbox{-} 250 \qquad \mbox{mW} \\ T_j \qquad \mbox{junction temperature} \qquad \mbox{-} 150 \ \ ^{\circ}\text{C} \\ T_{amb} \qquad \mbox{ambient temperature} \qquad \mbox{-} 65 \qquad \mbox{+} 150 \ ^{\circ}\text{C} \\ $	V _{EBO}	emitter-base voltage	open collector	-	-6	V
$t_p \le 1 \text{ ms}$ I_{BM} peak base currentsingle pulse; $t_p \le 1 \text{ ms}$ 100mA P_{tot} total power dissipation $T_{amb} \le 25 \text{ °C}$ [1]-250mW T_j junction temperature-150°C T_{amb} ambient temperature-65+150°C	I _C	collector current		-	-100	mA
$\label{eq:total_power_dissipation} t_p \leq 1 \text{ ms}$ $P_{tot} total power dissipation T_{amb} \leq 25 \ ^{\circ}\text{C} \qquad \begin{tabular}{lllllllllllllllllllllllllllllllllll$	I _{CM}	peak collector current	• •	-	-200	mA
T_jjunction temperature-150°CT_{amb}ambient temperature-65+150°C	I _{BM}	peak base current	• •	-	-100	mA
T_{amb} ambient temperature $-65 +150$ °C	P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	250	mW
	Tj	junction temperature		-	150	°C
T_{stg} storage temperature -65 +150 °C	T _{amb}	ambient temperature		-65	+150	°C
•	T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

45 V, 100 mA PNP general-purpose transistor



6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	140	K/W

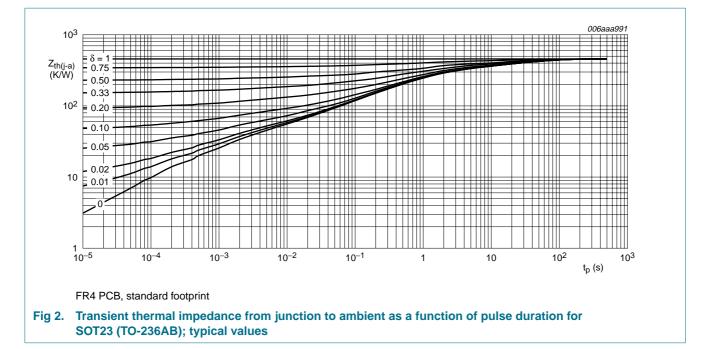
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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7. Characteristics

Table 7.Characteristics

 $T_{amb} = 25 \circ C$ unless otherwise specified.

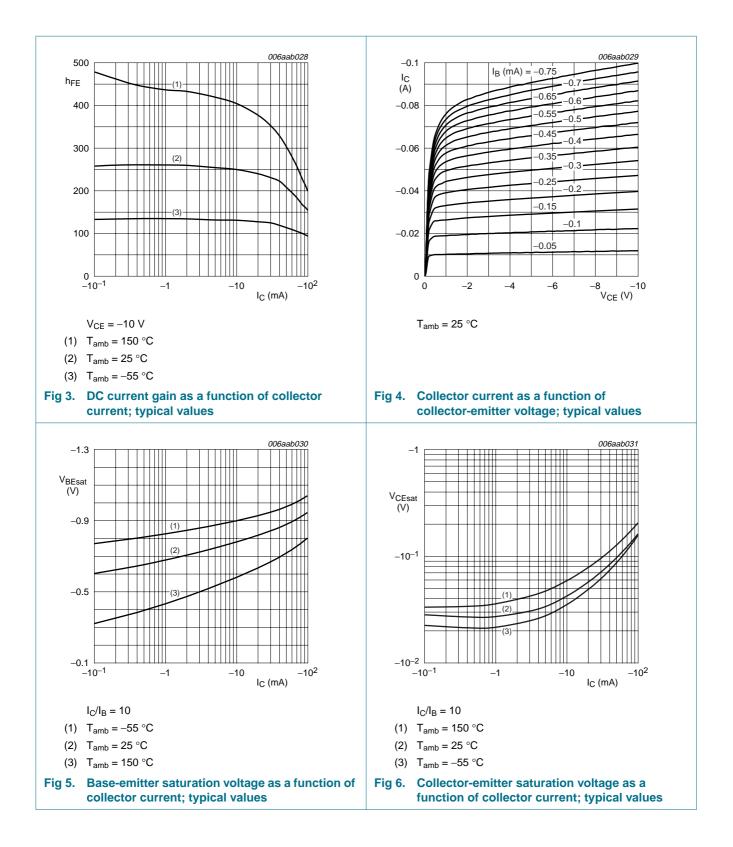
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -45 \text{ V}; \text{ I}_{\text{E}} = 0 \text{ A}$		-	-	-10	nA
	current	$V_{CB} = -45 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$		-	-	-5	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-10	nA
h _{FE}	DC current gain	$V_{CE} = -10 \text{ V};$ $I_C = -2 \text{ mA}$		210	-	340	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C} = -100 \text{ mA};$ $I_{\rm B} = -10 \text{ mA}$	<u>[1]</u>	-	-	-500	mV
f _T	transition frequency	$V_{CE} = -10 V;$ $I_{C} = -1 mA;$ f = 100 MHz		70	-	-	MHz
C _c	collector capacitance	$V_{CB} = -10 V;$ $I_E = i_e = 0 A;$ f = 1 MHz		-	-	5	pF

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

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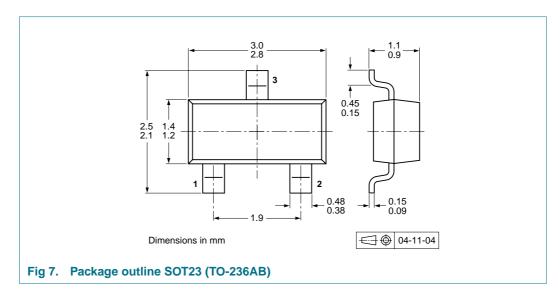
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8. Package outline



9. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing qu	antity
			3000	10000
2PB709ART	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

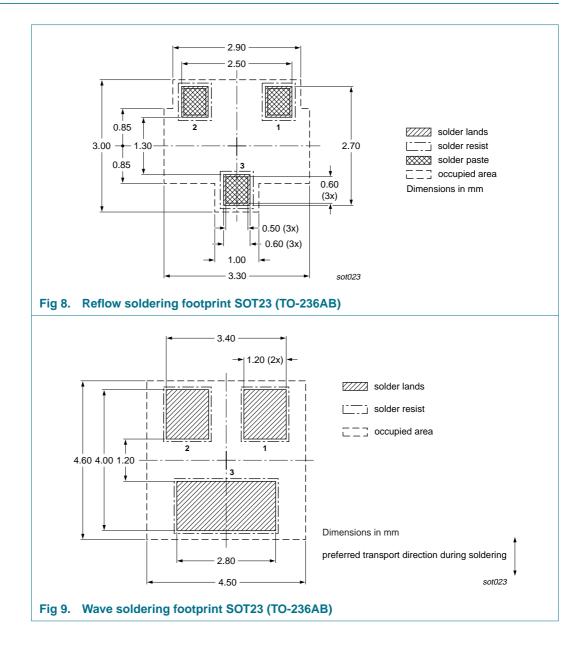
[1] For further information and the availability of packing methods, see <u>Section 13</u>.

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10. Soldering



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11. Revision history

Table 9. Revision his	Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
2PB709ART_1	20070319	Product data sheet	-	-			

45 V, 100 mA PNP general-purpose transistor

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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